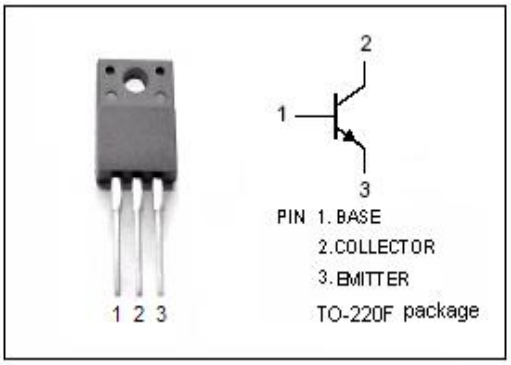
isc Silicon NPN Power Transistor — 2SC3565

DESCRIPTION

- High Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= 300V(Min)
- Good Linearity of h_{FE}
- Low Saturation Voltage
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

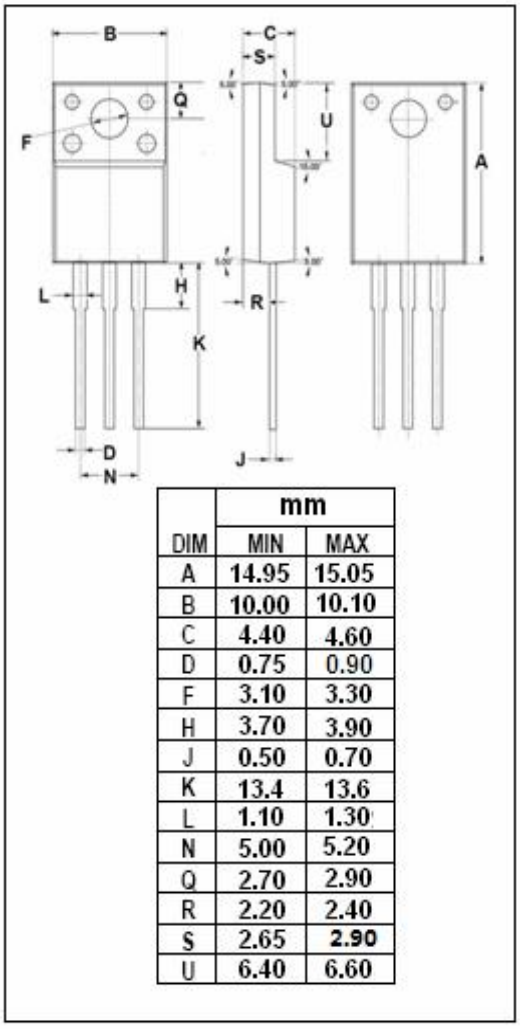


APPLICATIONS

- Designed for use in high frequency high voltage amplifier and TV viedo output applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	300	V
V_{CEO}	Collector-Emitter Voltage	300	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	0.2	A
P_C	Collector Power Dissipation @ T_C=25℃	15	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-40~150	℃



DIM	mm MIN	mm MAX
A	14.95	15.05
B	10.00	10.10
C	4.40	4.60
D	0.75	0.90
F	3.10	3.30
H	3.70	3.90
J	0.50	0.70
K	13.4	13.6
L	1.10	1.30
N	5.00	5.20
Q	2.70	2.90
R	2.20	2.40
S	2.65	2.90
U	6.40	6.60

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= 10 μ A ; I_E= 0	300			V
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 1mA ; R_{BE}= ∞	300			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Vltage	I_E= 10 μ A ; I_C= 0	7			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 20mA; I_B= 2mA			1.5	V
I_{CEO}	Collector Cutoff Current	V_{CE}= 250V; R_{BE}= ∞			1	μ A
h_{FE}	DC Current Gain	I_C= 10mA; V_{CE}= 10V	30		200	
f_T	Current-Gain—Bandwidth Product	I_C= 10mA; V_{CE}= 20V		80		MHz